

Please amend claim 1 as follows. Attached hereto is a marked-up copy of the amended claim.

- sub 1. (Twice Amended) A method of fabricating a semiconductor device, the method comprising the steps of:
- (a) forming a silicon oxynitride film on a silicon substrate;
 - (b) performing a heat treatment while keeping a surface of the silicon oxynitride film in contact with a gas containing nitrogen and oxygen to introduce at least nitrogen into the silicon oxynitride film;
 - (c) after step (b), forming a semiconductor film containing an impurity of first conductivity type on the silicon oxynitride film;
 - (d) after step (c), forming a gate electrode composed of the semiconductor film by patterning the semiconductor film;
 - (e) after step (d), forming a gate insulating film composed of the silicon oxynitride film by patterning the silicon oxynitride film.

REMARKS

The Office Action of **August 23, 2002** has been received and its contents carefully noted. Applicant thanks the Examiner for the consideration given the present application and submits that this response is timely filed and fully responsive to the Office Action.